

MUR20010CTR

MUR20010CTR Information

| www.heleecom | MUR20010CTR GeneSiC Semiconductor Discrete Semiconductor Products Diodes - Rectifiers - Arrays DIODE MODULE 100V 200A 2TOWER Twin Tower For the pricing/inventory/lead time, please contact | |
|--------------------|---|--|
| For Reference Only | website: https://www.heisener.com E-mail: salesdept@heisener.com | |





Request a Quote

Certified Quality

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.



MUR20010CTR Specifications

| Manufacturer GeneSic Semiconductor Category Discrete Semiconductor Products Diodes - Rectifiers - Arrays Diodes - Rectifiers - Arrays Package Twin Tower Series - Diode Configuration 1 Pair Common Anode Diode Type Schottky Voltage - DC Reverse (Vr) (Max) 100V Current - Average Rectified (Io) (per Diode) 200A (DC) Voltage - Forward (Vf) (Max) @ If 1.3V @ 100A Speed Fast Recovery =< 500ns, > 200mA (Io) Reverse Recovery Time (trr) 75ns Current - Reverse Leakage @ Vr 25µA @ 50V Operating Temperature - Junction -55°C ~ 150°C Mounting Type Chassis Mount | | |
|--|--|--------------------------------------|
| CategoryDiscrete Semiconductor ProductsPackageDiodes - Rectifiers - ArraysPackageTwin TowerSeries-Diode Configuration1 Pair Common AnodeDiode TypeSchottkyVoltage - DC Reverse (Vr) (Max)100VCurrent - Average Rectified (Io) (per Diode)200A (DC)Voltage - Forward (Vf) (Max) @ If1.3V @ 100ASpeedFast Recovery =< 500ns, > 200mA (Io)Reverse Recovery Time (trr)75nsCurrent - Reverse Leakage @ Vr25µA @ 50VOperating Temperature - Junction-55°C ~ 150°CMounting TypeChasis MountPackage / CaseTwin TowerSupplier Device PackageTwin Tower | Manufacturer Part Number | MUR20010CTR |
| Diodes - Rectifiers - ArraysPackageTwin TowerSeries-Diode Configuration1 Pair Common AnodeDiode TypeSchottkyVoltage - DC Reverse (Vr) (Max)100VCurrent - Average Rectified (Io) (per Diode)200A (DC)Voltage - Forward (Vf) (Max) @ If1.3V @ 100ASpeedFast Recovery =< 500ns, > 200mA (Io)Reverse Recovery Time (trr)75nsCurrent - Reverse Leakage @ Vr25μA @ 50VOperating Temperature - Junction-55°C ~ 150°CMounting TypeChassis MountPackage / CaseTwin TowerSupplier Device PackageTwin Tower | Manufacturer | GeneSiC Semiconductor |
| PackageTwin TowerSeries-Diode Configuration1 Pair Common AnodeDiode TypeSchottkyVoltage - DC Reverse (Vr) (Max)100VCurrent - Average Rectified (Io) (per Diode)200A (DC)Voltage - Forward (Vf) (Max) @ If1.3V @ 100ASpeedFast Recovery =< 500ns, > 200mA (Io)Reverse Recovery Time (trr)75nsCurrent - Reverse Leakage @ Vr25µA @ 50VOperating Temperature - Junction-55°C ~ 150°CMounting TypeChasis MountPackage / CaseTwin TowerSupplier Device PackageTwin Tower | Category | Discrete Semiconductor Products |
| Series-Series-Diode Configuration1 Pair Common AnodeDiode TypeSchottkyVoltage - DC Reverse (Vr) (Max)100VCurrent - Average Rectified (Io) (per Diode)200A (DC)Voltage - Forward (Vf) (Max) @ If1.3V @ 100ASpeedFast Recovery = < 500ns, > 200mA (Io)Reverse Recovery Time (trr)75nsCurrent - Reverse Leakage @ Vr25µA @ 50VOperating Temperature - Junction-55°C ~ 150°CMounting TypeChassis MountPackage / CaseTwin TowerSupplier Device PackageTwin Tower | | Diodes - Rectifiers - Arrays |
| Diode Configuration1 Pair Common AnodeDiode TypeSchottkyVoltage - DC Reverse (Vr) (Max)100VCurrent - Average Rectified (Io) (per Diode)200A (DC)Voltage - Forward (Vf) (Max) @ If1.3V @ 100ASpeedFast Recovery =< 500ns, > 200mA (Io)Reverse Recovery Time (trr)75nsCurrent - Reverse Leakage @ Vr25µA @ 50VOperating Temperature - Junction-55°C ~ 150°CMounting TypeChassis MountPackage / CaseTwin TowerSupplier Device PackageTwin Tower | Package | Twin Tower |
| Diode TypeSchottkyDiode TypeSchottkyVoltage - DC Reverse (Vr) (Max)100VCurrent - Average Rectified (Io) (per Diode)200A (DC)Voltage - Forward (Vf) (Max) @ If1.3V @ 100ASpeedFast Recovery =< 500ns, > 200mA (Io)Speed75nsCurrent - Reverse Leakage @ Vr25µA @ 50VOperating Temperature - Junction-55°C ~ 150°CMounting TypeChassis MountPackage / CaseTwin TowerSupplier Device PackageTwin Tower | Series | - |
| Voltage - DC Reverse (Vr) (Max)100VCurrent - Average Rectified (Io) (per Diode)200A (DC)Voltage - Forward (Vf) (Max) @ If1.3V @ 100ASpeedFast Recovery =< 500ns, > 200mA (Io)Reverse Recovery Time (trr)75nsCurrent - Reverse Leakage @ Vr25µA @ 50VOperating Temperature - Junction-55°C ~ 150°CMounting TypeChassis MountPackage / CaseTwin TowerSupplier Device PackageTwin Tower | Diode Configuration | 1 Pair Common Anode |
| Current - Average Rectified (Io) (per Diode)200A (DC)Voltage - Forward (Vf) (Max) @ If1.3V @ 100ASpeedFast Recovery =< 500ns, > 200mA (Io)Reverse Recovery Time (trr)75nsCurrent - Reverse Leakage @ Vr25µA @ 50VOperating Temperature - Junction-55°C ~ 150°CMounting TypeChassis MountPackage / CaseTwin TowerSupplier Device PackageTwin Tower | Diode Type | Schottky |
| Voltage - Forward (Vf) (Max) @ If1.3V @ 100ASpeedFast Recovery =< 500ns, > 200mA (Io)Reverse Recovery Time (trr)75nsCurrent - Reverse Leakage @ Vr25µA @ 50VOperating Temperature - Junction-55°C ~ 150°CMounting TypeChassis MountPackage / CaseTwin TowerSupplier Device PackageTwin Tower | Voltage - DC Reverse (Vr) (Max) | 100V |
| SpeedFast Recovery =< 500ns, > 200mA (Io)Reverse Recovery Time (trr)75nsCurrent - Reverse Leakage @ Vr25µA @ 50VOperating Temperature - Junction-55°C ~ 150°CMounting TypeChassis MountPackage / CaseTwin TowerSupplier Device PackageTwin Tower | Current - Average Rectified (Io) (per Diode) | 200A (DC) |
| Reverse Recovery Time (trr)75nsCurrent - Reverse Leakage @ Vr25µA @ 50VOperating Temperature - Junction-55°C ~ 150°CMounting TypeChassis MountPackage / CaseTwin TowerSupplier Device PackageTwin Tower | Voltage - Forward (Vf) (Max) @ If | 1.3V @ 100A |
| Current - Reverse Leakage @ Vr25μA @ 50VOperating Temperature - Junction-55°C ~ 150°CMounting TypeChassis MountPackage / CaseTwin TowerSupplier Device PackageTwin Tower | Speed | Fast Recovery =< 500ns, > 200mA (Io) |
| Operating Temperature - Junction-55°C ~ 150°CMounting TypeChassis MountPackage / CaseTwin TowerSupplier Device PackageTwin Tower | Reverse Recovery Time (trr) | 75ns |
| Mounting TypeChassis MountPackage / CaseTwin TowerSupplier Device PackageTwin Tower | Current - Reverse Leakage @ Vr | 25μA @ 50V |
| Package / Case Twin Tower Supplier Device Package Twin Tower | Operating Temperature - Junction | -55°C ~ 150°C |
| Supplier Device Package Twin Tower | Mounting Type | Chassis Mount |
| | Package / Case | Twin Tower |
| Report errors? | Supplier Device Package | Twin Tower |
| | | Report errors? |

MUR20010CTR Guarantees



Quality Guarantees

We provide 90 days warranty. * If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.

SERVICE BUARANTEE

Service Guarantees

We guarantee 100% customer satisfaction. Our experienced sales team and tech support team back our services to satisfy all our customers.

MUR20010CTR Payment Methods



MUR20010CTR Shipping Methods



If you have any question about MUR20010CTR, please do not hesitate to contact us! Website: https://www.heisener.com E-mail: salesdept@heisener.com